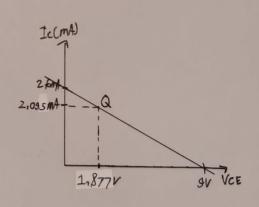
```
1. Bdc = 200
   AC = ZLSL
   VEC=100
   RB = 2204 SL
  VBB-AV
 IN VEF = VCC-ICRC , VCE-10 - 10RC
 IC = VOC -VCE
           RC
  IC= 10-VCE
                                     Ic(MA)
          2/2
  Vce = on Ic= 5 mA
  IC =0, VEE = 10V
 IB = VBB- VEE
                                   5mA
           RB
                                  3,6mA
        9 = 1,8 x10 5 A
                                               2,81
                                                                  VCE
Ic = 200 x (1,8 x 10-5)
     = 020036A
 VCE= VCC-ICRC
      =10v-(0,0036)(2h)
2. Bdc=200
  Rc = 4702
  vcc = 5V
  RB = 514 D
  VBB = 5 V
                         VETVBTVE
 IB = VBB+VEE
                         7,89679,2070,7
    = 5+0,7=8 A3X10-5A
                         . Transistor dalam kondisi ahtif
     514
 Ic=Bdc=IB
= 200.8193X10-5A
    = 1,68×10-2A
 VB = IB · RB
= &193×10-5.51k
    = 9,20V
 Ve=Ic-RC
    =1,68×102 . 970
= 7,896V
 VE=0,7V
```



Ir 20 -7 VEE = AV

$$IE = \frac{V_E}{RE} = \frac{4^3}{3h} = 1,43 \text{ mA} \approx IC$$

$$rc = \frac{RC \cdot RL}{Rc + RL} = \frac{5h \cdot 10h}{Sh + 10h} = \frac{50M}{15h} = 3,33h \Omega$$

$$AV = \frac{rc}{rei} = \frac{3,38c}{17,482} = 190,981$$